

Rev.A Feb.-2024

TO-252 N MOS

N-CHANNEL MOSFET in a TO-252 Plastic Package.

H_{fs} / H_{fs} /

Low gate charge, low crss, fast switching, HF Product. Have good Electromagnetic Interference performance, HF Product.

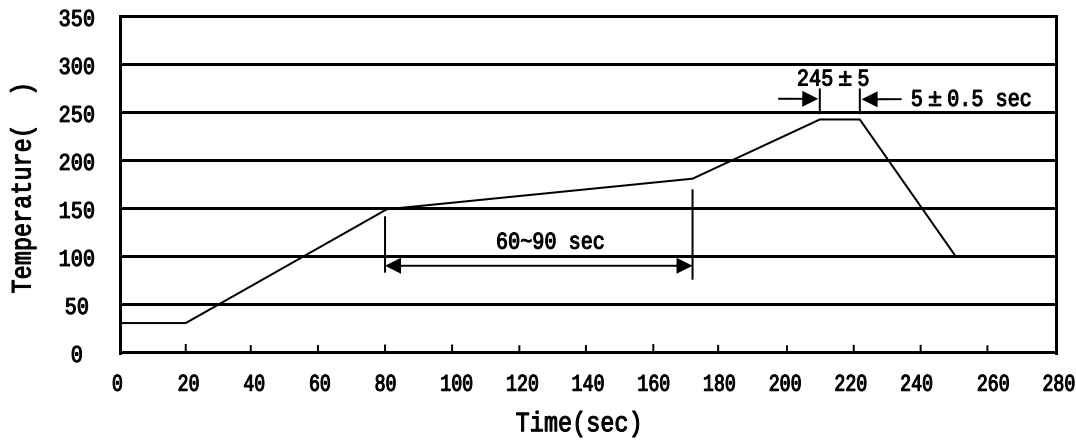
These devices are well suited for power switch circuit of adaptor and charger.

PIN1 G PIN 2 D PIN 3

Parameter	^N Symbol	Rating	^H Unit
Drain-Source Voltage	V_{DS}	500	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	3	A
Drain Current - Pulsed	I_{DM}	6	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	97	mJ
Avalanche Current	I_{AS}	4.4	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	45	W

Parameter	N Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	td(on)	V _{DD} =100V I _D =3.0A V _{GS} =10V R _G =25Ω		4		ns

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 °C , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 °C , Duration:5±0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 °C/sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13 ×16	360×360×50	380×335×366

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180